

Low-power JFET dual operational amplifiers

Features

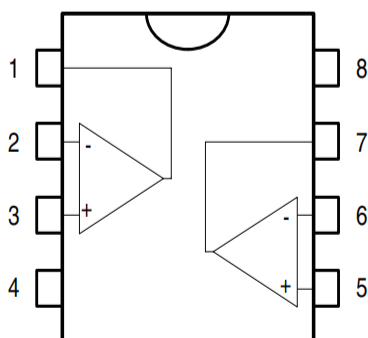
- Very low power consumption: 200 μ A
- Wide common-mode (up to V_{CC}^+) and differential voltage ranges
- Low input bias and offset currents
- Output short-circuit protection
- High input impedance JFET input stage
- Internal frequency compensation
- Latch up free operation
- High slew rate: 3.5 V/ μ s

Description

The TL062, TL062A and TL062B devices are high-speed JFET input single operational amplifiers. Each of these JFET input operational amplifiers incorporates well matched, high-voltage JFET and bipolar transistors in a monolithic integrated circuit.

The devices feature high slew rates, low input bias and offset currents, and a low offset voltage temperature coefficient.

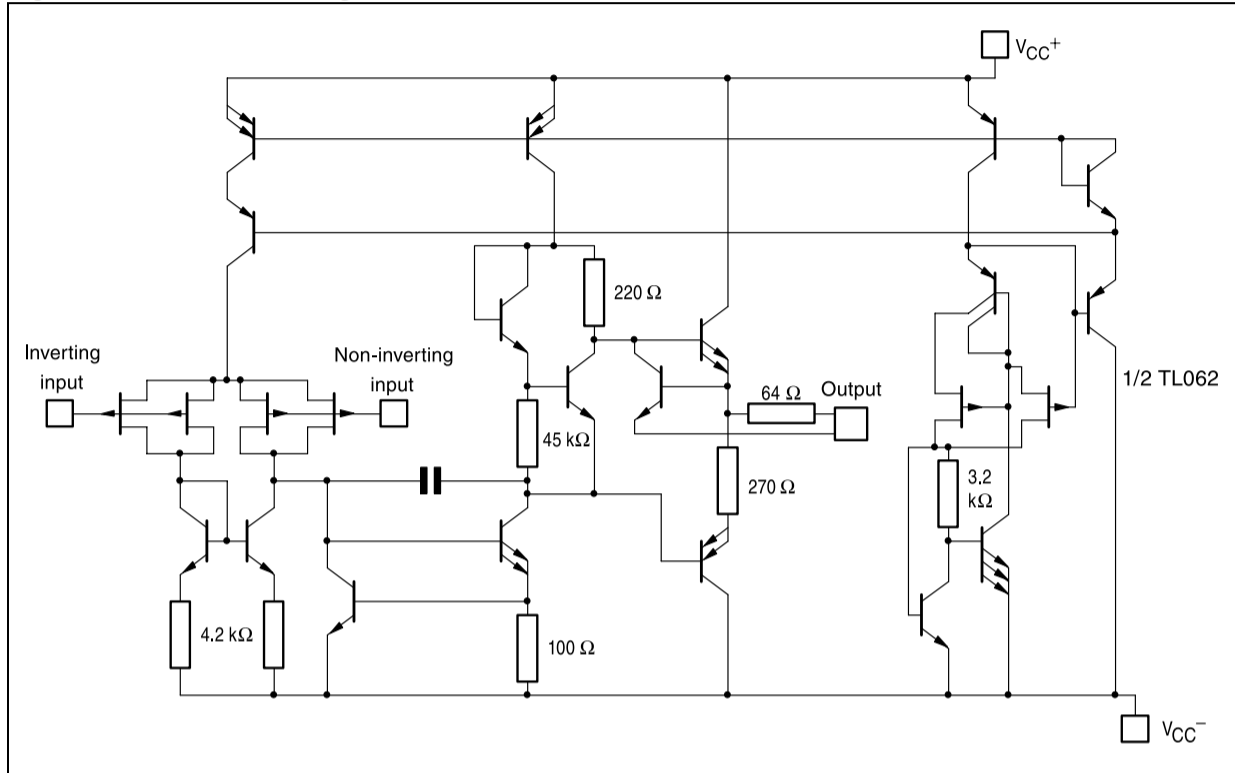
Pin connections (top view)



- 1 - Output 1
- 2 - Inverting input 1
- 3 - Non-inverting input 1
- 4 - V_{CC}^-
- 5 - Non-inverting input 2
- 6 - Inverting input 2
- 7 - Output 2
- 8 - V_{CC}^+

1 Schematic diagram

Figure 1. Schematic diagram



2 Absolute maximum ratings and operating conditions

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage ⁽¹⁾	±18	V
V _i	Input voltage ⁽²⁾	±15	V
V _{id}	Differential input voltage ⁽³⁾	±30	V
P _{tot}	Power dissipation	680	mW
	Output short-circuit duration ⁽⁴⁾	Infinite	
T _{stg}	Storage temperature range		°C
R _{thja}	Thermal resistance junction-to-ambient ^{(5), (6)}		°C/W
	SO-8	125	
	DIP8	85	
R _{thjc}	Thermal resistance junction-to-case ^{(5), (6)}		°C/W
	SO-8	40	
	DIP8	41	
ESD	HBM: human body model ⁽⁷⁾	900	V
	MM: machine model ⁽⁸⁾	150	V
	CDM: charged device model ⁽⁹⁾	1.5	kV

- All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between V_{CC}⁺ and V_{CC}⁻.
- The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
- Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
- The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.
- Short-circuits can cause excessive heating and destructive dissipation.
- R_{th} are typical values.
- Human body model: 100 pF discharged through a 1.5 kΩ resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
- Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω), done for all couples of pin combinations with other pins floating.
- Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to ground.

Table 2. Operating conditions

Symbol	Parameter	TL062I, AI, BI	TL062C, AC, BC	Unit
V _{CC}	Supply voltage range	6 to 36		V
T _{oper}	Operating free air temperature range	-40 to +105	0 to +70	°C

3 Electrical characteristics

Table 3. $V_{CC} = \pm 15\text{ V}$, $T_{amb} = +25\text{ °C}$ (unless otherwise specified)

Symbol	Parameter	TL062I			TL062C			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input offset voltage ($R_S = 50\ \Omega$) $T_{amb} = +25\text{ °C}$ $T_{min} \leq T_{amb} \leq T_{max}$		3	6 9		3	15 20	mV
DV_{io}	Temperature coefficient of input offset voltage ($R_S = 50\ \Omega$)		10			10		$\mu\text{V}/\text{°C}$
I_{io}	Input offset current ⁽¹⁾ $T_{amb} = +25\text{ °C}$ $T_{min} \leq T_{amb} \leq T_{max}$		5	100 10		5	200 5	pA nA
I_{ib}	Input bias current ⁽¹⁾ $T_{amb} = +25\text{ °C}$ $T_{min} \leq T_{amb} \leq T_{max}$		30	200 20		30	400 10	pA nA
V_{icm}	Input common mode voltage range	± 11.5	+15 -12		± 11.5	+15 -12		V
V_{opp}	Output voltage swing ($R_L = 10\ \text{k}\Omega$) $T_{amb} = +25\text{ °C}$ $T_{min} \leq T_{amb} \leq T_{max}$	20 20	27		20 20	27		V
A_{vd}	Large signal voltage gain $R_L = 10\ \text{k}\Omega$, $V_o = \pm 10\ \text{V}$, $T_{amb} = +25\text{ °C}$ $T_{min} \leq T_{amb} \leq T_{max}$	4 4	6		3 3	6		V/mV
GBP	Gain bandwidth product $T_{amb} = +25\text{ °C}$, $R_L = 10\ \text{k}\Omega$, $C_L = 100\ \text{pF}$		1			1		MHz
R_i	Input resistance		10^{12}			10^{12}		Ω
CMR	Common mode rejection ratio $R_S = 50\ \Omega$	80	86		70	76		dB
SVR	Supply voltage rejection ratio $R_S = 50\ \Omega$	80	95		70	95		dB
I_{CC}	Supply current, no load $T_{amb} = +25\text{ °C}$, no load, no signal		200	250		200	250	μA
V_{o1}/V_{o2}	Channel separation $A_v = 100$, $T_{amb} = 25\text{ °C}$		120			120		dB
P_D	Total power consumption $T_{amb} = +25\text{ °C}$, no load, no signal		6	7.5		6	7.5	mW
SR	Slew rate $V_i = 10\ \text{V}$, $R_L = 10\ \text{k}\Omega$, $C_L = 100\ \text{pF}$, $A_v = 1$	1.5	3.5		1.5	3.5		V/ μs

Table 3. $V_{CC} = \pm 15\text{ V}$, $T_{amb} = +25\text{ }^\circ\text{C}$ (unless otherwise specified) (continued)

Symbol	Parameter	TL062I			TL062C			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
t_r	Rise time $V_i = 20\text{ mV}$, $R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_v = 1$		0.2			0.2		μs
K_{ov}	Overshoot factor (see <i>Figure 15</i>) $V_i = 20\text{ mV}$, $R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_v = 1$		10			10		%
e_n	Equivalent input noise voltage $R_S = 100\text{ }\Omega$, $f = 1\text{ kHz}$		42			42		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$

1. The input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.

Table 4. $V_{CC} = \pm 15\text{ V}$, $T_{amb} = +25\text{ }^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	TL062AC, AI			TL062BC, BI			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{io}	Input offset voltage ($R_S = 50\text{ }\Omega$) $T_{amb} = +25\text{ }^\circ\text{C}$ $T_{min} \leq T_{amb} \leq T_{max}$		3	3 7.5		2	3 5	mV
DV_{io}	Temperature coefficient of input offset voltage ($R_S = 50\text{ }\Omega$)		10			10		$\mu\text{V}/^\circ\text{C}$
I_{io}	Input offset current ⁽¹⁾ $T_{amb} = +25\text{ }^\circ\text{C}$ $T_{min} \leq T_{amb} \leq T_{max}$		5	100 3		5	100 3	pA nA
I_{ib}	Input bias current ⁽¹⁾ $T_{amb} = +25\text{ }^\circ\text{C}$ $T_{min} \leq T_{amb} \leq T_{max}$		30	200 7		30	200 7	nA
V_{icm}	Input common mode voltage range	± 11.5	+15 -12		± 11.5	+15 -12		
V_{opp}	Output voltage swing ($R_L = 10\text{ k}\Omega$) $T_{amb} = +25\text{ }^\circ\text{C}$ $T_{min} \leq T_{amb} \leq T_{max}$	20 20	27		20 20	27		V
A_{vd}	Large signal voltage gain $R_L = 10\text{ k}\Omega$, $V_o = \pm 10\text{ V}$, $T_{amb} = +25\text{ }^\circ\text{C}$ $T_{min} \leq T_{amb} \leq T_{max}$	4 4	6		4 4	6		V/mV
GBP	Gain bandwidth product $T_{amb} = +25\text{ }^\circ\text{C}$, $R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$		1			1		MHz
R_i	Input resistance		10^{12}			10^{12}		Ω
CMR	Common mode rejection ratio $R_S = 50\text{ }\Omega$	80	86		80	86		dB
SVR	Supply voltage rejection ratio $R_S = 50\text{ }\Omega$	80	95		80	95		dB

Table 4. $V_{CC} = \pm 15\text{ V}$, $T_{amb} = +25\text{ °C}$ (unless otherwise specified) (continued)

Symbol	Parameter	TL062AC, AI			TL062BC, BI			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
I_{CC}	Supply current, no load $T_{amb} = +25\text{ °C}$, no load, no signal		200	250		200	250	μA
V_{o1}/V_{o2}	Channel separation $A_v = 100$, $T_{amb} = +25\text{ °C}$		120			120		
P_D	Total power consumption $T_{amb} = +25\text{ °C}$, no load, no signal		6	7.5		6	7.5	mW
SR	Slew rate $V_i = 10\text{ V}$, $R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_v = 1$	1.5	3.5		1.5	3.5		$\text{V}/\mu\text{s}$
t_r	Rise time $V_i = 20\text{ mV}$, $R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_v = 1$		0.2			0.2		μs
K_{ov}	Overshoot factor (see <i>Figure 15</i>) $V_i = 20\text{ mV}$, $R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_v = 1$		10			10		%
e_n	Equivalent input noise voltage $R_S = 100\ \Omega$, $f = 1\text{ kHz}$		42			42		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$

1. The input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.

Figure 2. Maximum peak-to-peak output voltage versus supply voltage

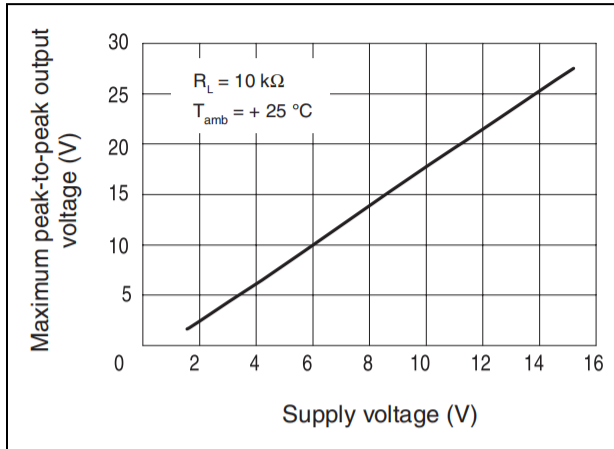


Figure 3. Maximum peak-to-peak output voltage versus free air temperature

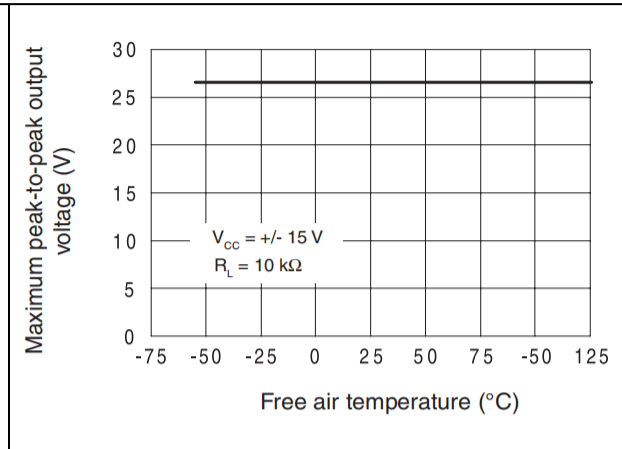


Figure 4. Maximum peak-to-peak output voltage versus load resistance

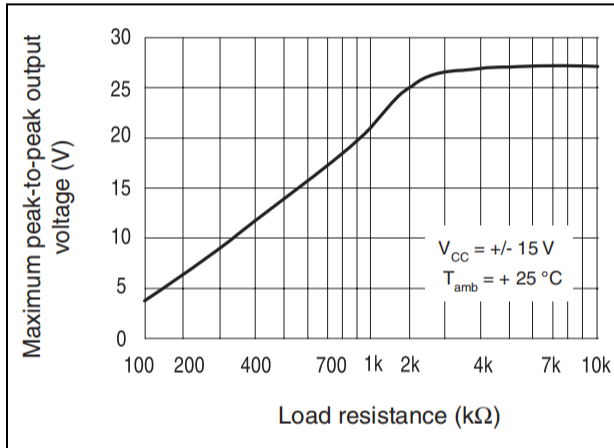


Figure 5. Maximum peak-to-peak output voltage versus frequency

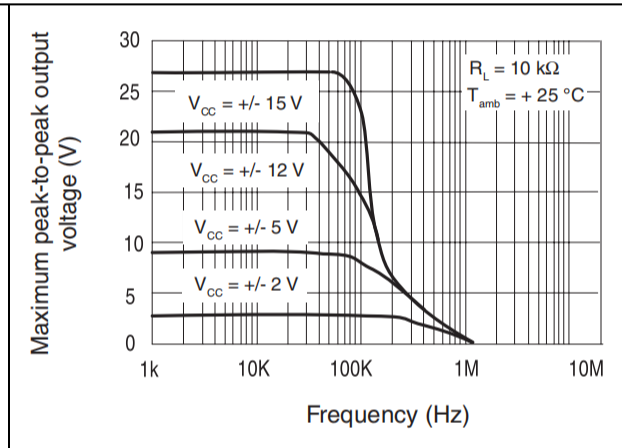


Figure 6. Differential voltage amplification versus free air temperature

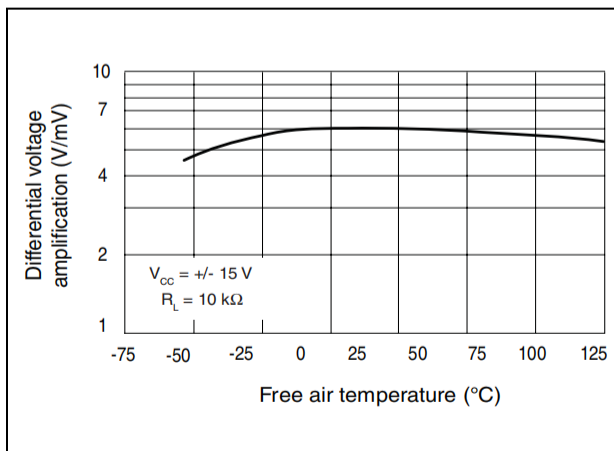


Figure 7. Large signal differential voltage amplification and phase shift versus frequency

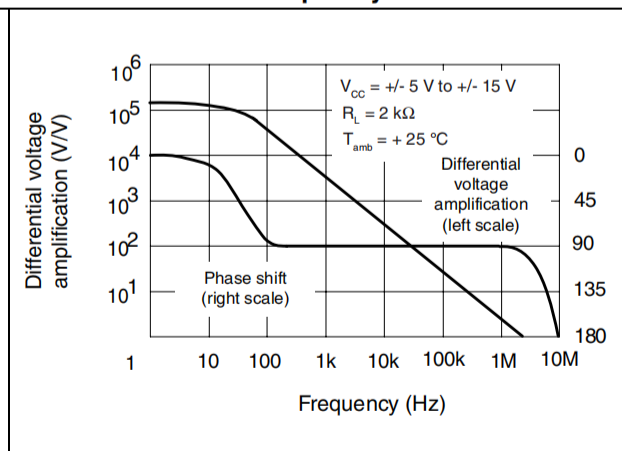


Figure 8. Supply current per amplifier versus supply voltage

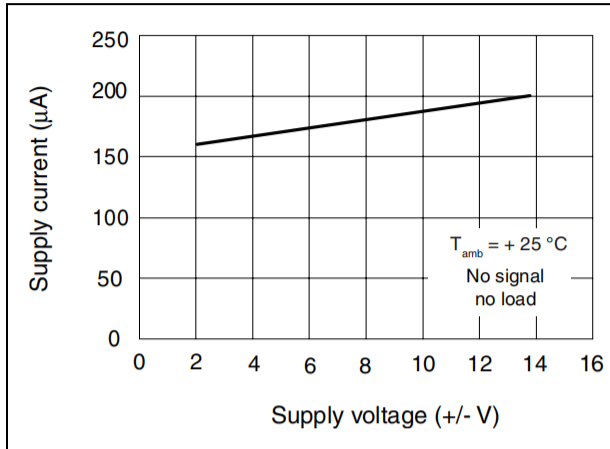


Figure 9. Supply current per amplifier versus free air temperature

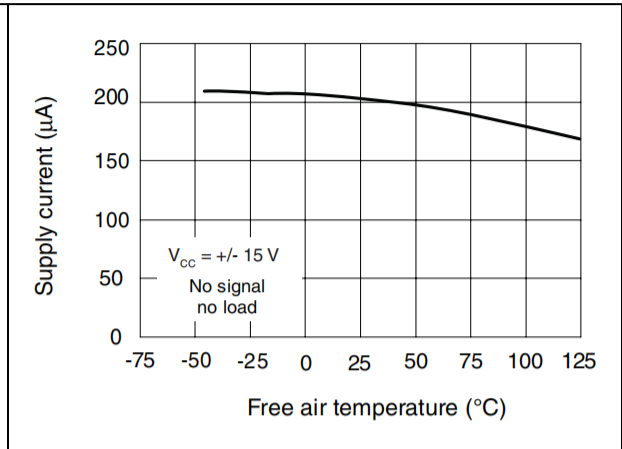


Figure 10. Total power dissipated versus free air temperature

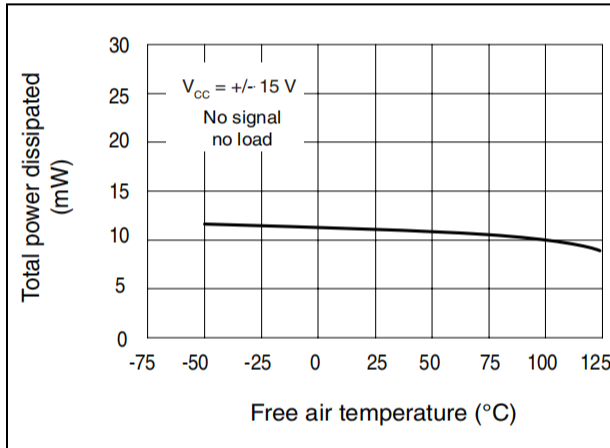


Figure 11. Common-mode rejection ratio versus free air temperature

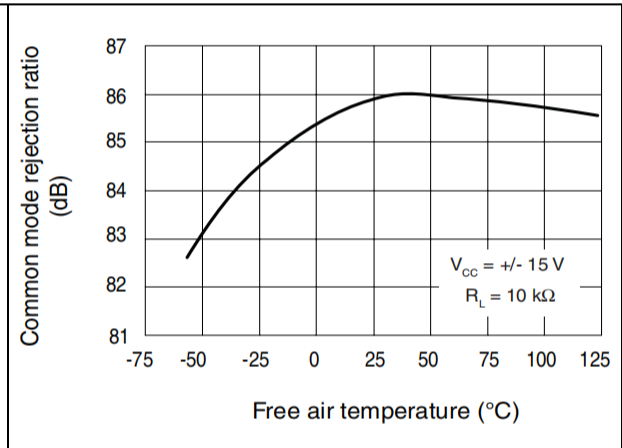


Figure 12. Normalized unity gain bandwidth, slew rate and phase shift versus temperature

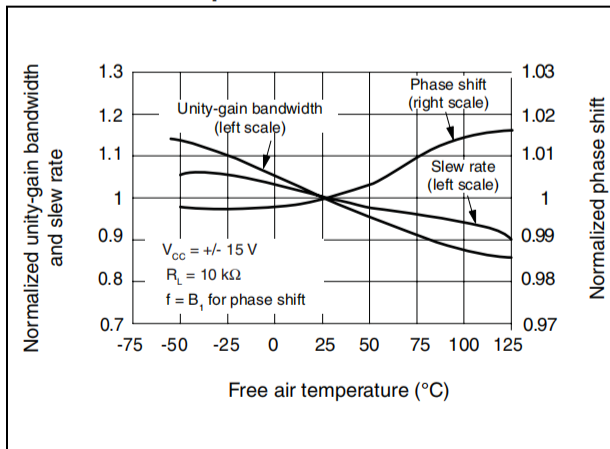


Figure 13. Input bias current versus free air temperature

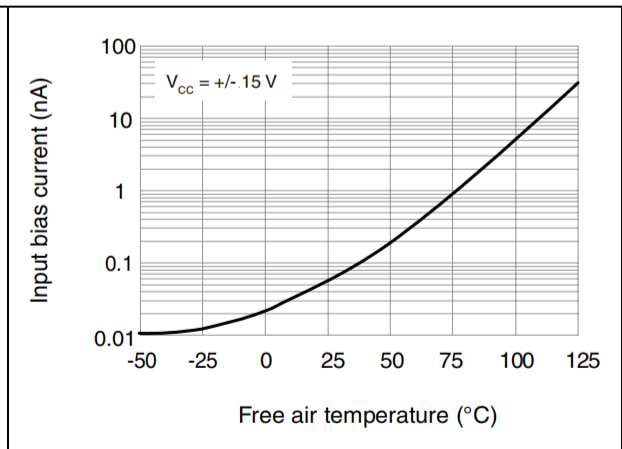


Figure 14. Voltage follower large signal pulse response

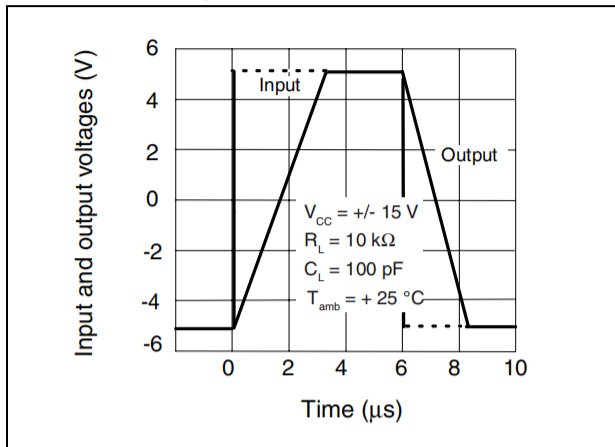


Figure 15. Output voltage versus elapsed time

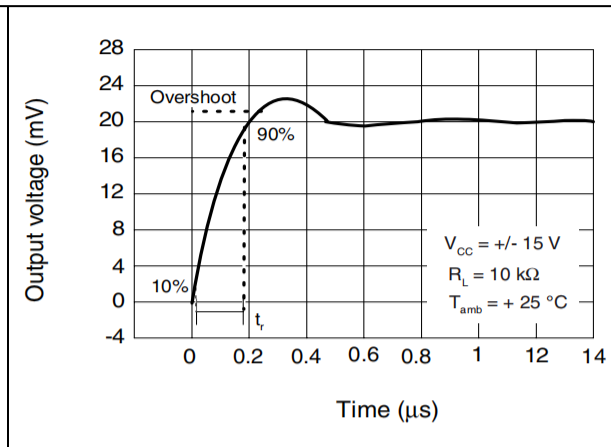
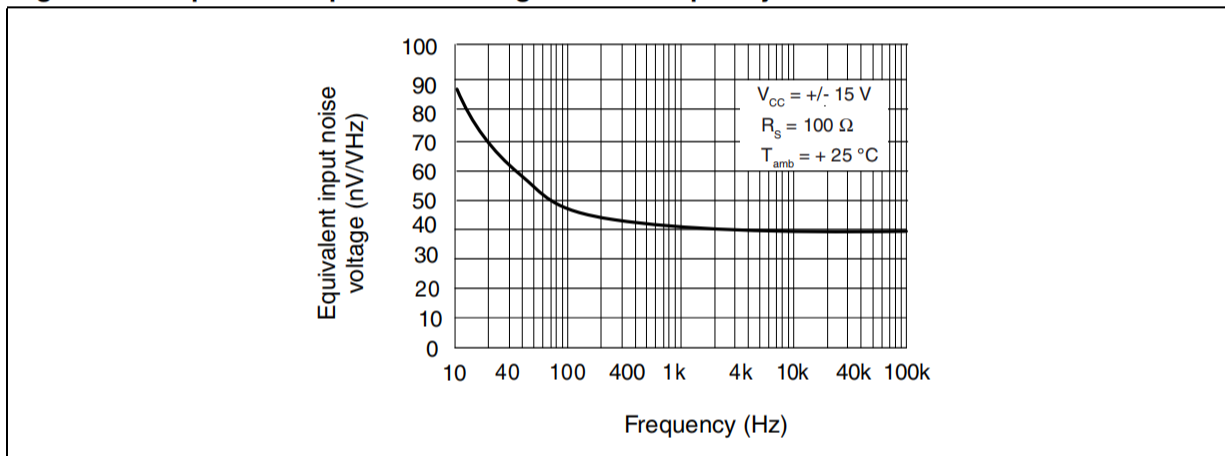


Figure 16. Equivalent input noise voltage versus frequency



Parameter measurement information

Figure 17. Voltage follower

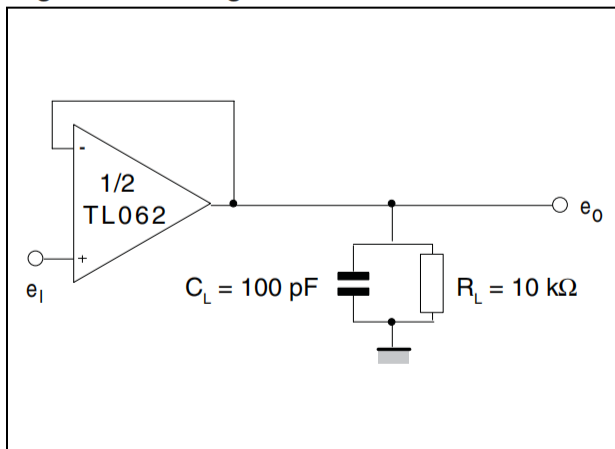
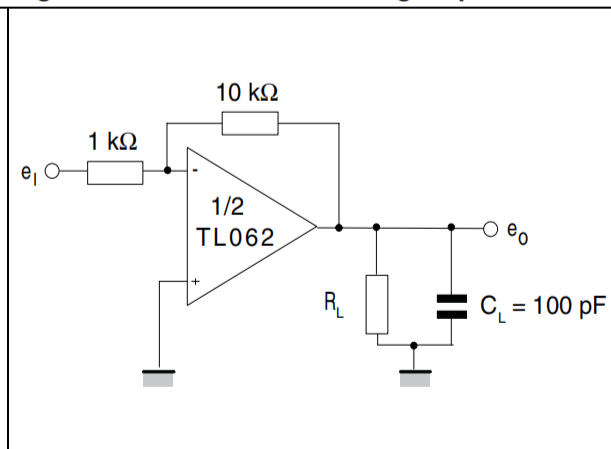
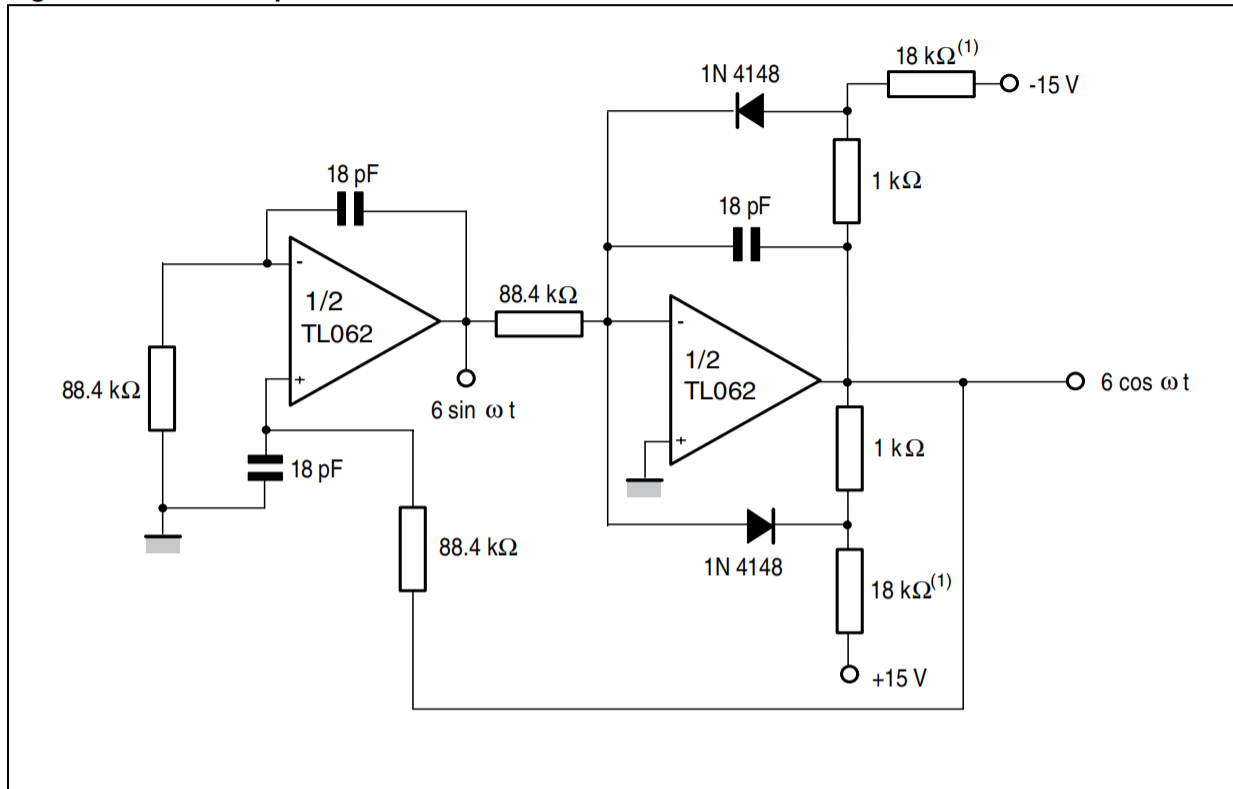


Figure 18. Gain of 10 inverting amplifier



4 Typical applications

Figure 19. 100 kHz quadrature oscillator



1. These resistor values may be adjusted for a symmetrical output.

5.1 DIP8 package information

Figure 20. DIP8 package outline

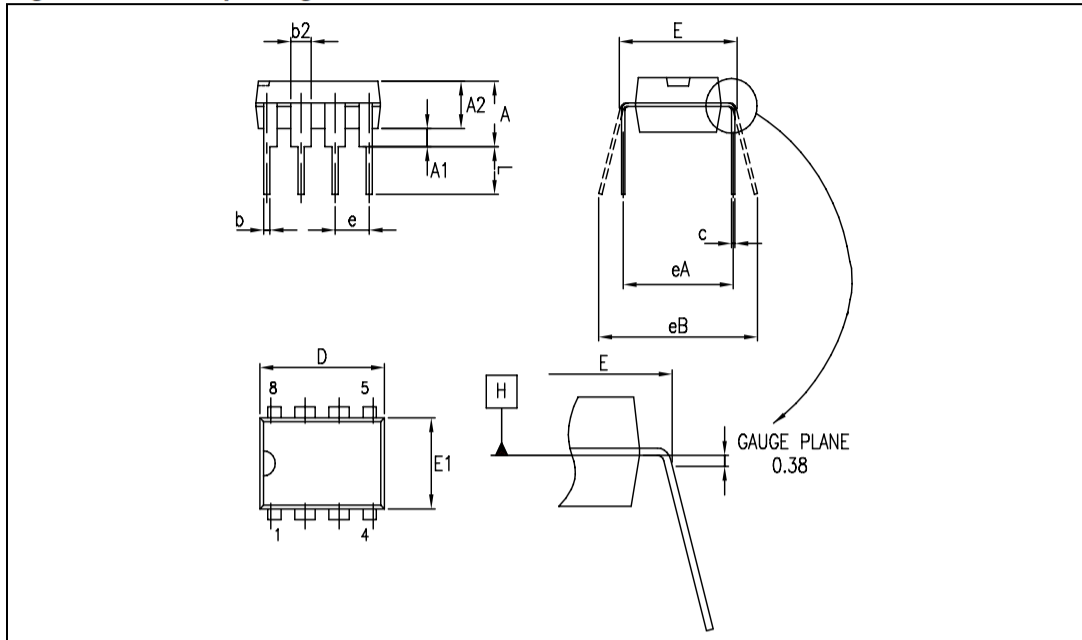


Table 5. DIP8 package mechanical data

Symbol	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			5.33			0.210
A1	0.38			0.015		
A2	2.92	3.30	4.95	0.115	0.130	0.195
b	0.36	0.46	0.56	0.014	0.018	0.022
b2	1.14	1.52	1.78	0.045	0.060	0.070
c	0.20	0.25	0.36	0.008	0.010	0.014
D	9.02	9.27	10.16	0.355	0.365	0.400
E	7.62	7.87	8.26	0.300	0.310	0.325
E1	6.10	6.35	7.11	0.240	0.250	0.280
e		2.54			0.100	
eA		7.62			0.300	
eB			10.92			0.430
L	2.92	3.30	3.81	0.115	0.130	0.150

Note: Dimensions "D" and "E1" do not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.25 mm in total (both sides). Datum plane "H" coincides with the bottom of the lead, where the lead exits the body.

5.2 SO-8 package information

Figure 21. SO-8 package outline

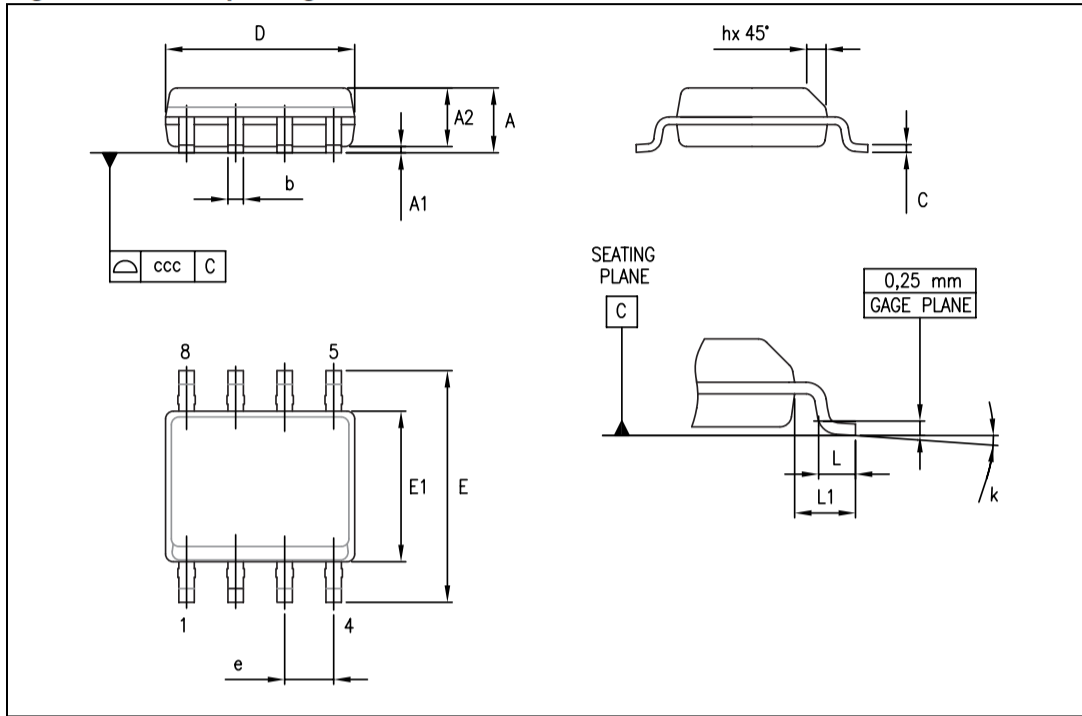


Table 6. SO-8 package mechanical data

Symbol	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
A1	0.10		0.25	0.004		0.010
A2	1.25			0.049		
b	0.28		0.48	0.011		0.019
c	0.17		0.23	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e		1.27			0.050	
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
L1		1.04			0.040	
k	0		8°	1°		8°
ccc			0.10			0.004